



N-Channel 60-V (D-S) 200°C MOSFET

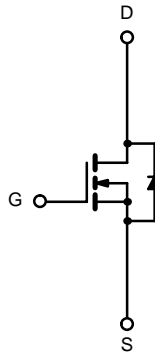
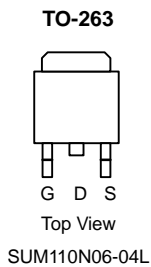
PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.0035 @ $V_{GS} = 10$ V	110 ^a
	0.005 @ $V_{GS} = 4.5$ V	

FEATURES

- TrenchFET® Power MOSFETS
- 200°C Junction Temperature
- New Low Thermal Resistance Package

APPLICATIONS

- Automotive
 - Boardnet 42-V EPS and ABS
 - Motor Drives
- High Current
- DC/DC Converters



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	110 ^a	A
		$T_C = 125^\circ\text{C}$	110 ^a	
Pulsed Drain Current	I_{DM}	440		
Avalanche Current	I_{AR}	75		
Repetitive Avalanche Energy ^b	E_{AR}	L = 0.1 mH	280	mJ
Maximum Power Dissipation ^b			$T_C = 25^\circ\text{C}$	
	$T_A = 25^\circ\text{C}$ ^d	3.7		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 200	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient—PCB Mount ^d	R_{thJA}	40	$^\circ\text{C}/\text{W}$
Junction-to-Case (Drain)	R_{thJC}	0.4	

Notes

- Package limited.
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	60			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V			1	μA
		V _{DS} = 48 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 48 V, V _{GS} = 0 V, T _J = 200 °C			10	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.0028	0.0035	Ω
		V _{GS} = 4.5 V, I _D = 20 A		0.004	0.005	
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.0058	
		V _{GS} = 10 V, I _D = 30 A, T _J = 200 °C			0.0088	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	30			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		7500		pF
Output Capacitance	C _{oss}			1050		
Reverse Transfer Capacitance	C _{rss}			700		
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 110 A		150	220	nC
Gate-Source Charge ^c	Q _{gs}			25		
Gate-Drain Charge ^c	Q _{gd}			45		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.4 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _G = 2.5 Ω		20	30	ns
Rise Time ^c	t _r			135	200	
Turn-Off Delay Time ^c	t _{d(off)}			80	120	
Fall Time ^c	t _f			150	220	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _S				110	A
Pulsed Current	I _{SM}				440	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.1	1.4	V
Reverse Recovery Time	t _{rr}	I _F = 110 A, di/dt = 100 A/μs		75	120	ns
Peak Reverse Recovery Current	I _{RM(REC)}			2.5	5	A
Reverse Recovery Charge	Q _{rr}			0.09	0.25	μC

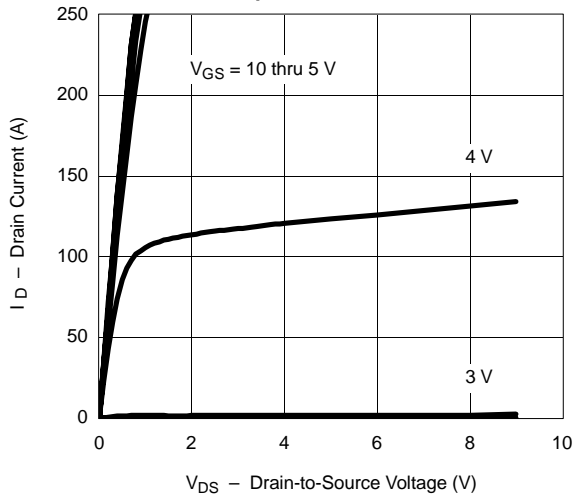
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

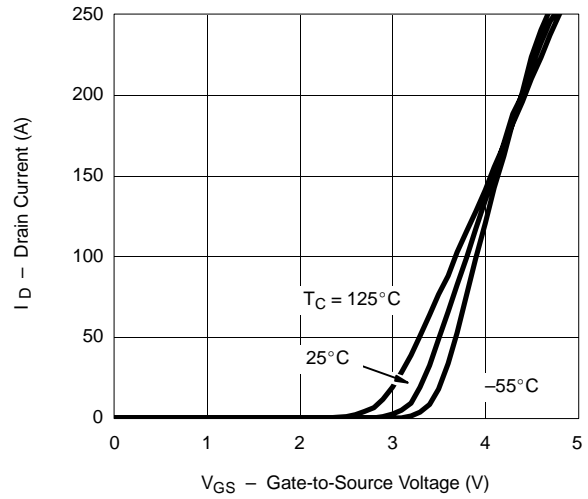


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

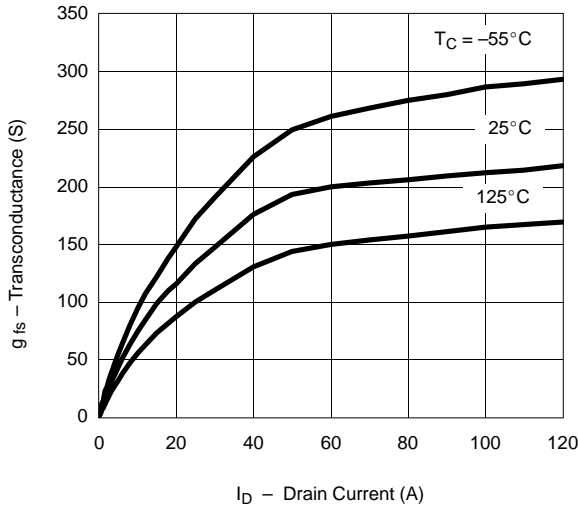
Output Characteristics



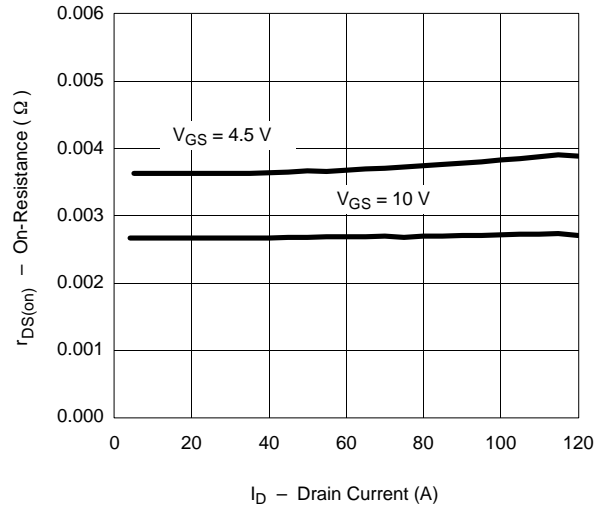
Transfer Characteristics



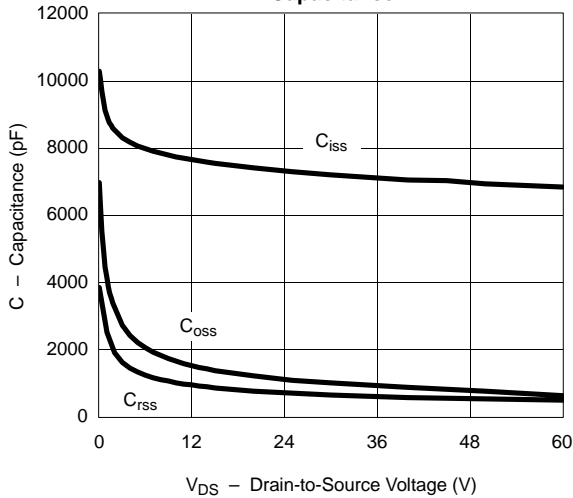
Transconductance



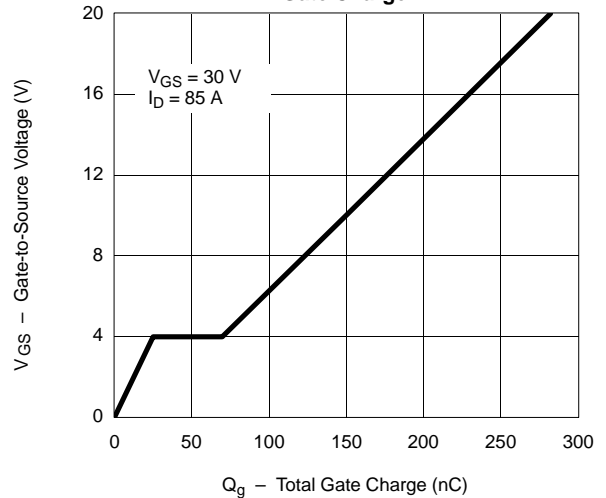
On-Resistance vs. Drain Current



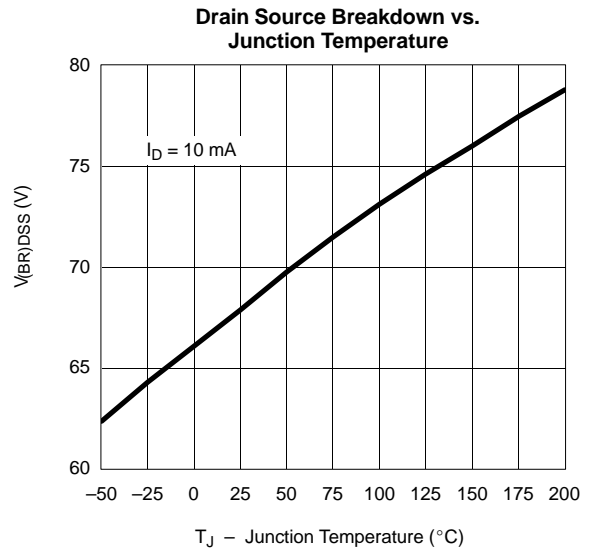
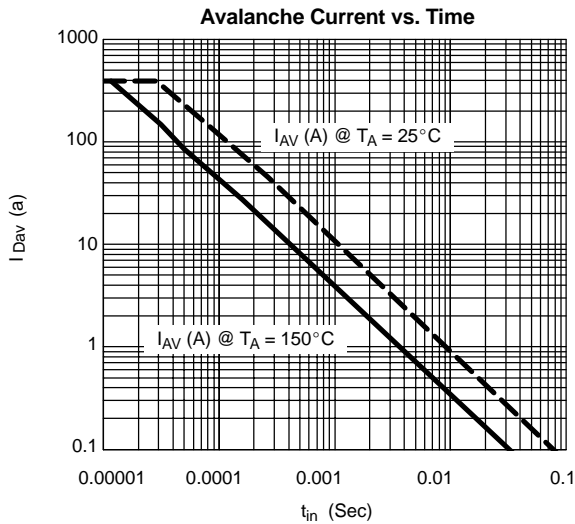
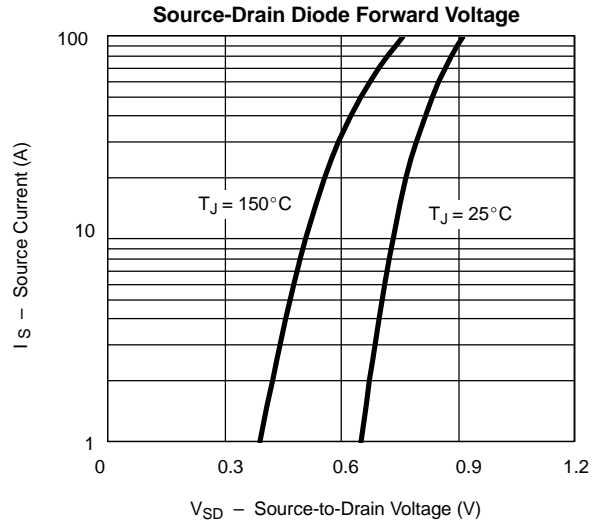
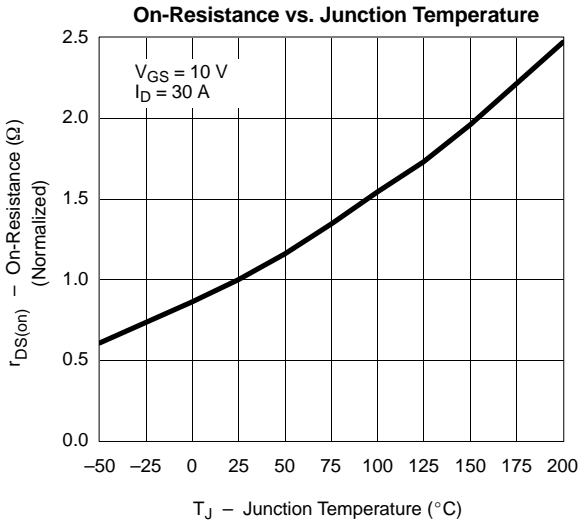
Capacitance



Gate Charge



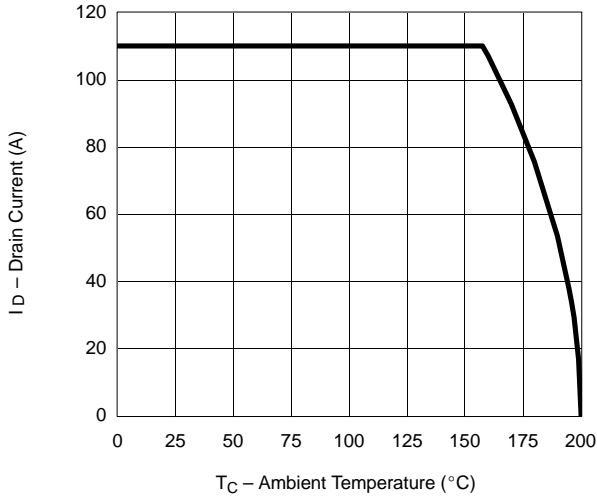
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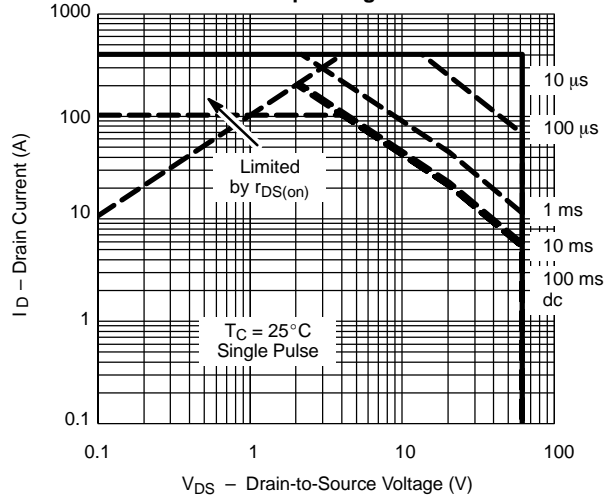


THERMAL RATINGS

Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

